

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π -MOSV)

2SK3443

Switching Regulator, DC-DC Converter and Motor Drive Applications

- Low drain-source ON resistance: $R_{DS(ON)} = 50 \text{ m}\Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 9 \text{ S}$ (typ.)
- Low leakage current: $I_{DSS} = 100 \text{ }\mu\text{A}$ ($V_{DS} = 150 \text{ V}$)
- Enhancement-mode: $V_{th} = 3.0 \text{ to } 5.0 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	150	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	150	V
Gate-source voltage		V_{GSS}	± 30	V
Drain current	DC (Note 1)	I_D	30	A
	Pulse (Note 1)	I_{DP}	120	
Drain power dissipation ($T_c = 25^\circ\text{C}$)		P_D	125	W
Single pulse avalanche energy (Note 2)		E_{AS}	468	mJ
Avalanche current		I_{AR}	30	A
Repetitive avalanche energy (Note 3)		E_{AR}	12.5	mJ
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	1.00	$^\circ\text{C/W}$

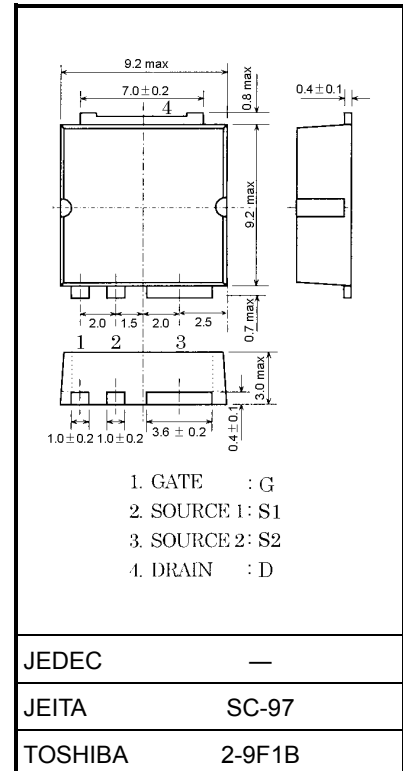
Note 1: Please use devices on condition that the channel temperature is below 150°C .

Note 2: $V_{DD} = 50 \text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 773 \text{ }\mu\text{H}$, $R_G = 25 \text{ }\Omega$, $I_{AR} = 30 \text{ A}$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm

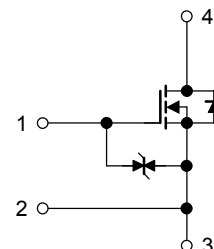


Weight: 0.74 g (typ.)

Circuit Configuration

Notice:

Please use the S1 pin for gate input signal return. Make sure that the main current flows into S2 pin.



Electrical Characteristics (Note 4) (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 10	μA
Drain cut-off current		I_{DSS}	$V_{DS} = 150 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	100	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	150	—	—	V
Gate threshold voltage		V_{th}	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	3.0	—	5.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$	—	50	55	$\text{m}\Omega$
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10 \text{ V}, I_D = 15 \text{ A}$	4.5	9	—	S
Input capacitance		C_{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	2030	—	pF
Reverse transfer capacitance		C_{rss}		—	340	—	
Output capacitance		C_{oss}		—	1200	—	
Switching time	Rise time	t_r		—	20	—	ns
	Turn-on time	t_{on}		—	40	—	
	Fall time	t_f		—	10	—	
	Turn-off time	t_{off}		—	40	—	
Total gate charge (gate-source plus gate-drain)		Q_g	$V_{DD} \approx 120 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	—	45	—	nC
Gate-source charge		Q_{gs}		—	21	—	
Gate-drain ("miller") charge		Q_{gd}		—	24	—	

Note 4: Please connect the S1 pin and S2 pin, and then ground the connected pin.
(However, while switching times are measured, please don't connect and ground it.)

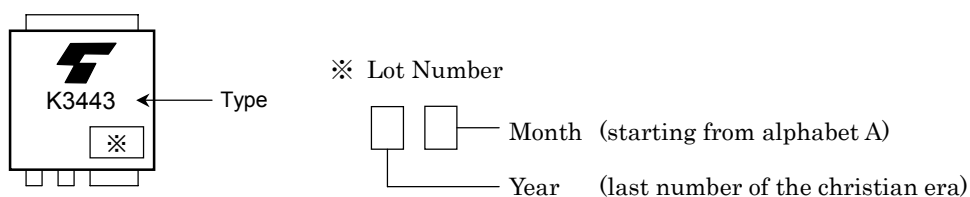
Source-Drain Diode Ratings and Characteristics (Note 5) (Ta = 25°C)

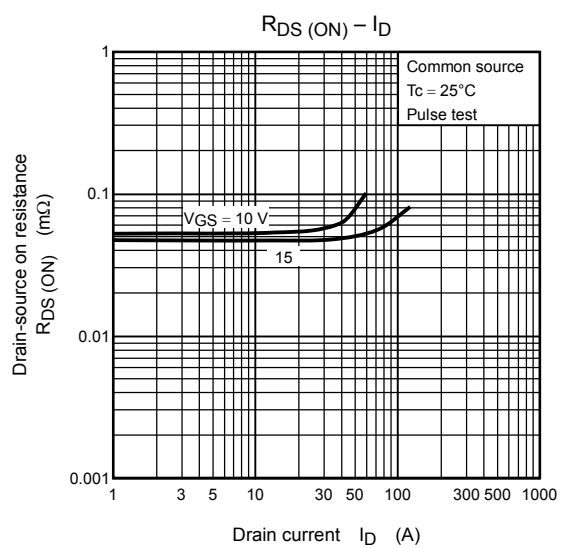
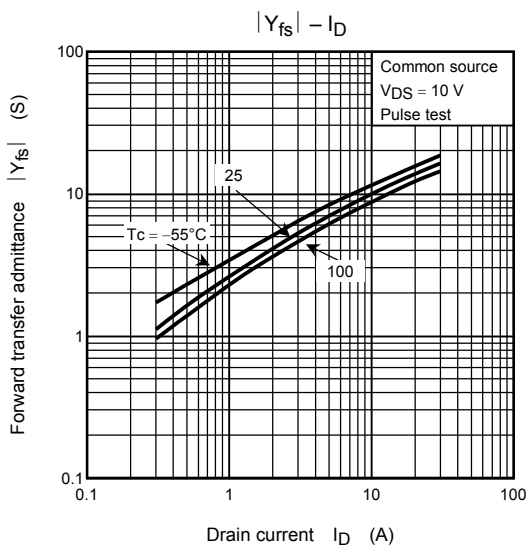
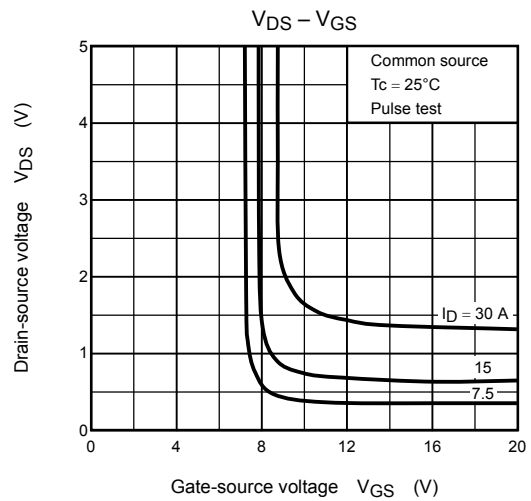
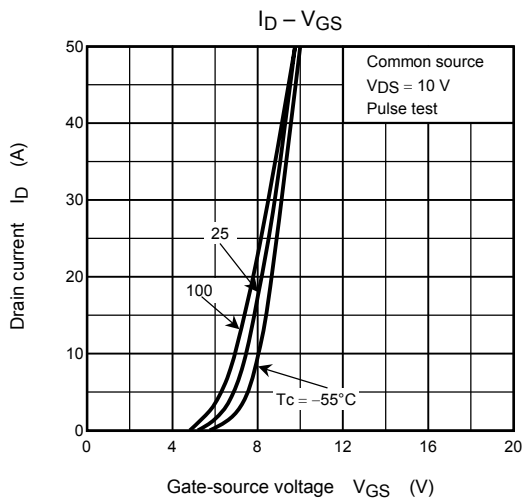
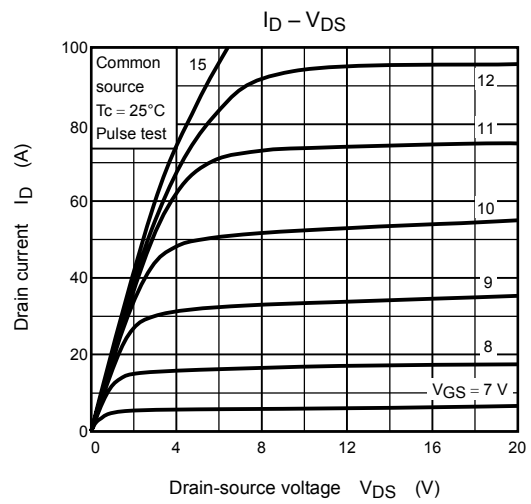
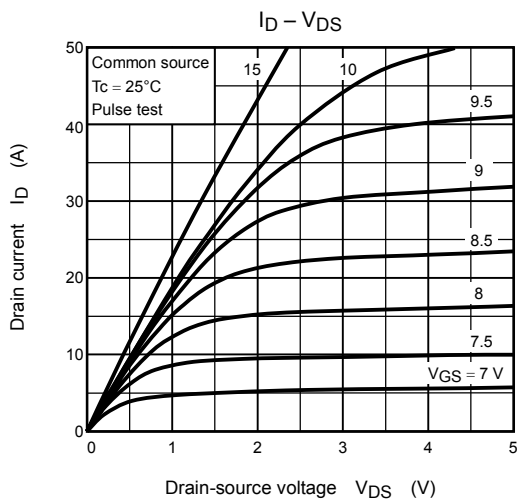
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1, Note 5)	I_{DR1}	—	—	—	30	A
Pulse drain reverse current (Note 1, Note 5)	I_{DRP1}	—	—	—	120	A
Continuous drain reverse current (Note 1, Note 5)	I_{DR2}	—	—	—	1	A
Pulse drain reverse current (Note 1, Note 5)	I_{DRP2}	—	—	—	4	A
Forward voltage (diode)	V_{DS2F}	$I_{DR1} = 30 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.5	V
Reverse recovery time	t_{rr}	$I_{DR} = 30 \text{ A}, V_{GS} = 0 \text{ V},$	—	250	—	ns
Reverse recovery charge	Q_{rr}	$dI_{DR}/dt = 100 \text{ A}/\mu\text{s}$	—	1.75	—	μC

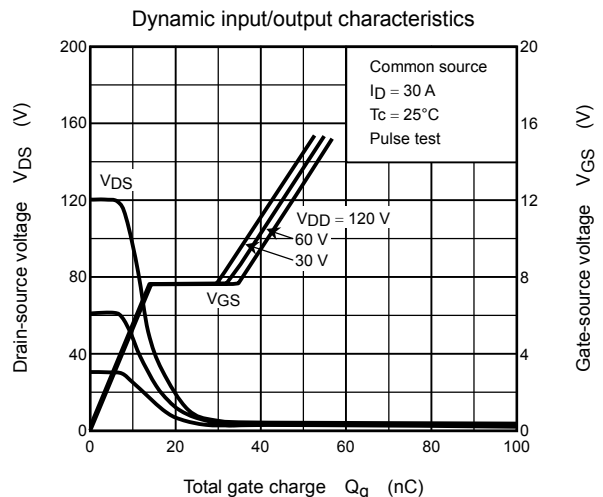
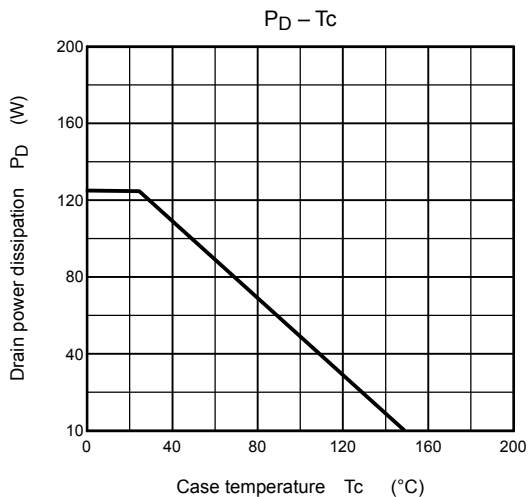
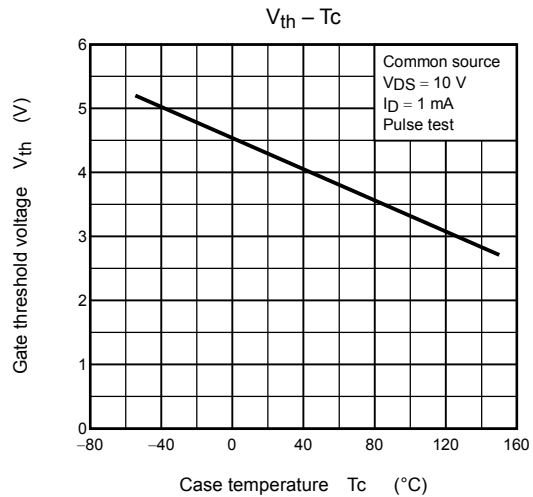
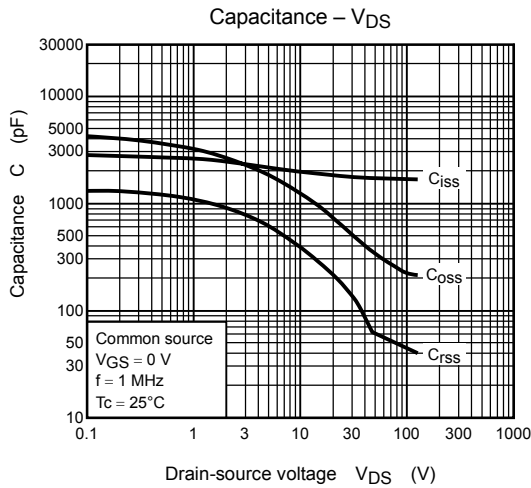
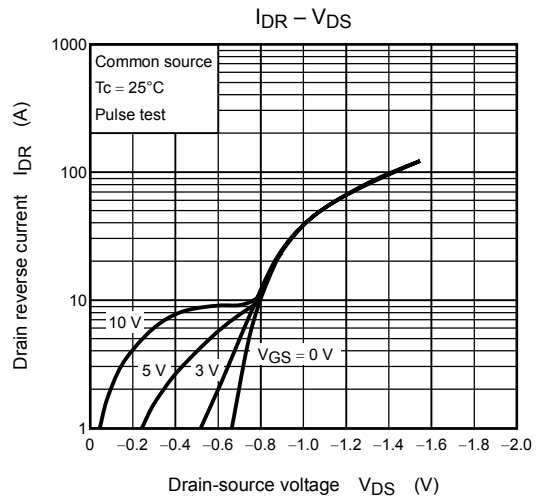
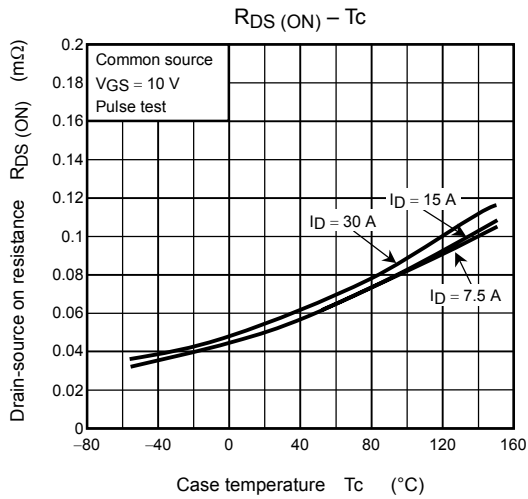
Note 5: drain, flowing current value between the S1 pin, open the S2 pin

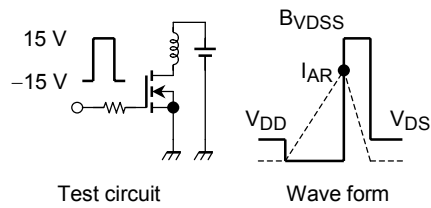
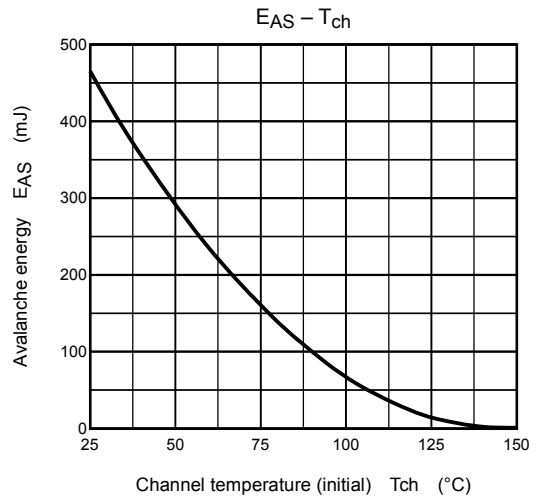
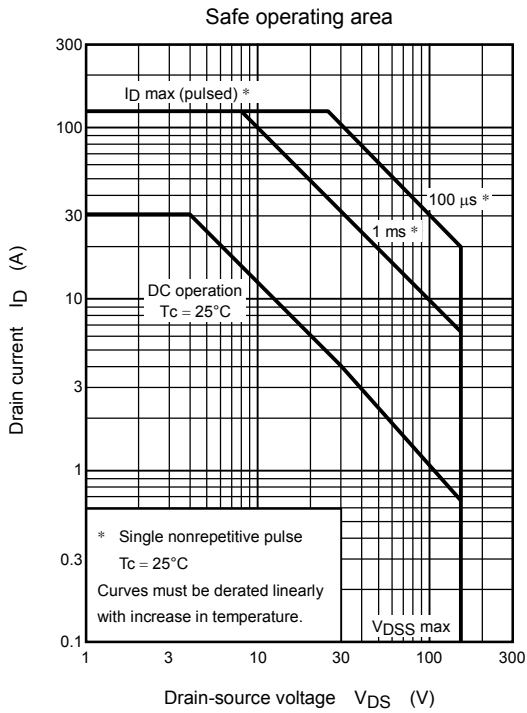
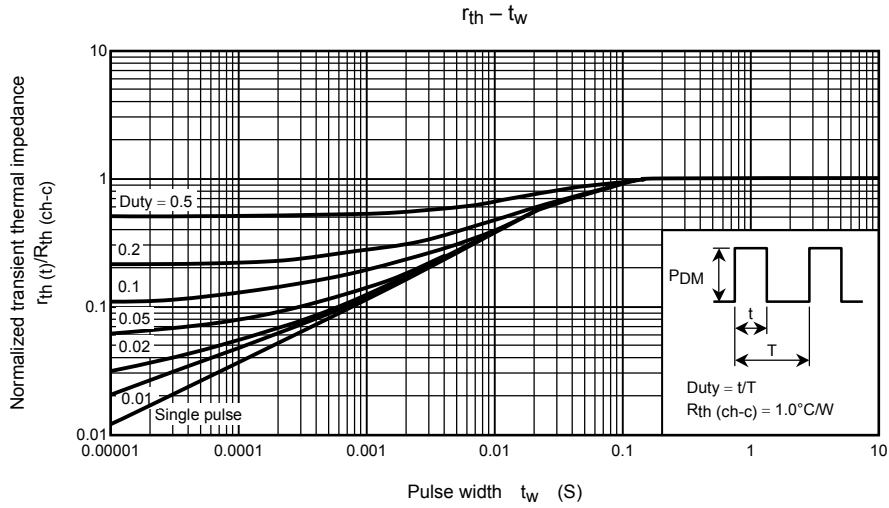
Unless otherwise specified, please connect the S1 and S2 pins, and then ground the connected pin.

Marking









$$R_G = 25 \Omega$$

$$V_{DD} = 50 \text{ V}, L = 773 \mu\text{H}$$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I_{AR}^2 \cdot \left(\frac{BVDSS}{BVDSS - V_{DD}} \right)$$

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